

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	18mΩ@4.5V	7A
	22mΩ@2.5V	
	39mΩ@1.8V	

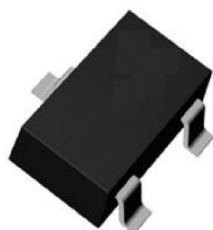
Feature

- Trench power LV MOSFET technology
- High speed switching
- ESD protected

Application

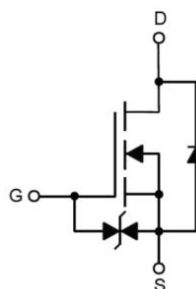
- PWM application
- Load switch

Package

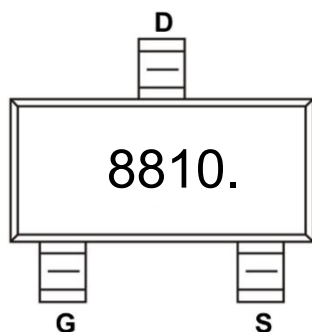


SOT-23

Circuit diagram



Marking



Absolute maximum ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Continuous Drain Current	I_D	7	A
Continuous Drain Current($T_A=100^{\circ}\text{C}$)	$I_D (100^{\circ}\text{C})$	4	A
Pulsed Drain Current ¹⁾	I_{DM}	40	A
Power Dissipation ²⁾	P_D	1.1	W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	113.6	$^{\circ}\text{C/W}$
Operating Junction Temperature	T_J	$-55 \sim +150$	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$

Electrical characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±10V			±10	μA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.45	0.7	1	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =7A		14	18	mΩ
		V _{GS} =2.5V, I _D =4A		17	22	
		V _{GS} =1.8V, I _D =1.5A		25	39	
Dynamic characteristics ³⁾						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f =1MHz		610		pF
Output Capacitance	C _{oss}			130		
Reverse Transfer Capacitance	C _{rss}			110		
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =10V, I _D =7A		12		nC
Gate-Source Charge	Q _{gs}			2		
Gate-Drain Charge	Q _{gd}			2.5		
Turn-on delay time	t _{d(on)}	V _{DS} =10V, V _{GS} =10V, I _D =7A R _G =2.2Ω		4		nS
Turn-on rise time	t _r			15		
Turn-off delay time	t _{d(off)}			18		
Turn-off fall time	t _f			8		
Source-Drain Diode characteristics						
Diode Forward Current	I _S				7	A
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =7A			1.2	V
Reverse recovery time	T _{rr}	I _F =7A,di/dt =100 A/μs		12		nS
Reverse recovery charge	Q _{rr}			1		nC

Notes:

- 1) Repetitive rating; pulse width limited by max. junction temperature
- 2) P_D is based on max. junction temperature, using junction-case thermal resistance
- 3) Guaranteed by design, not subject to production testing.

Typical Characteristics

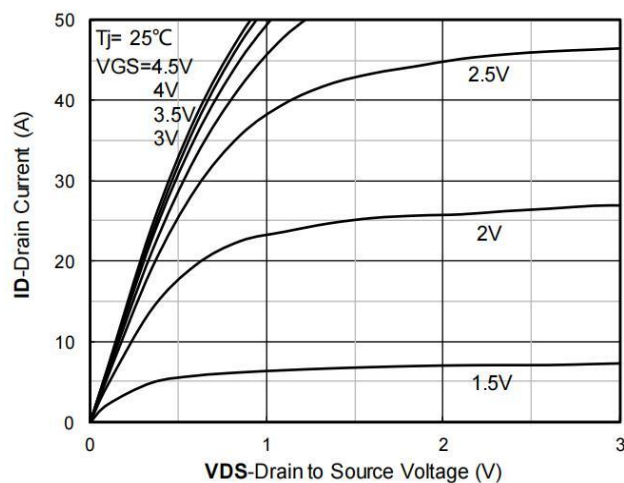


Figure 1. Output Characteristics

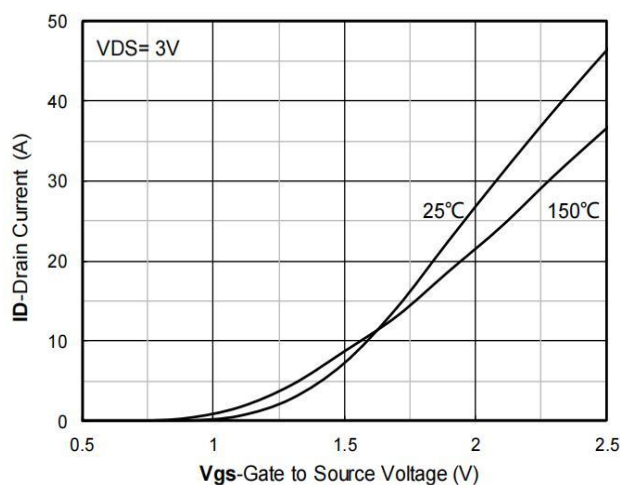


Figure 2. Transfer Characteristics

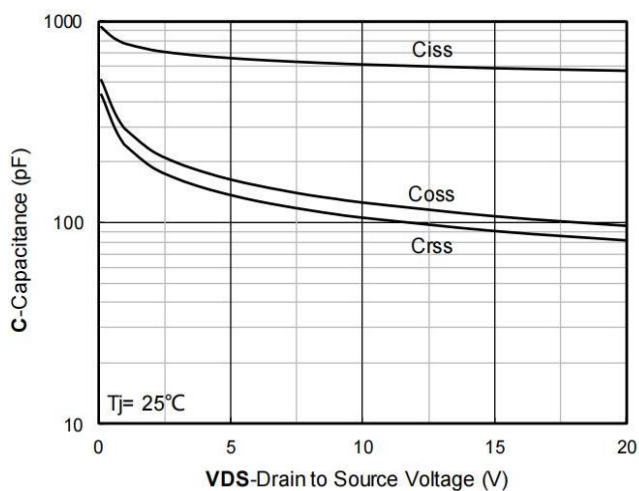


Figure 3. Capacitance Characteristics

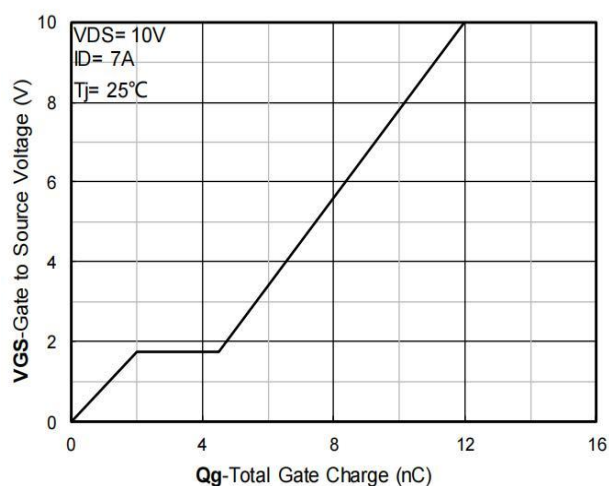


Figure 4. Gate Charge

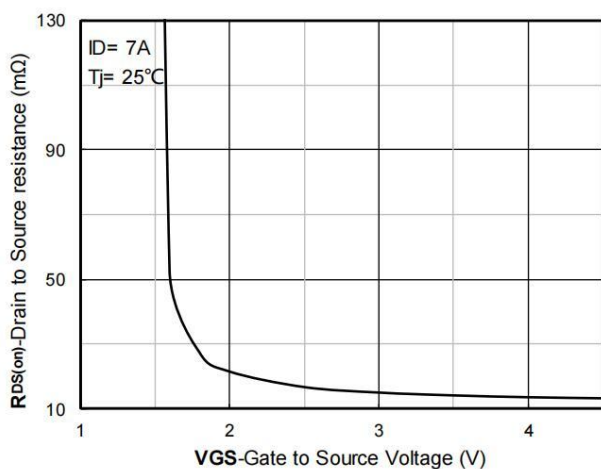


Figure 5. On-Resistance vs Gate to Source Voltage

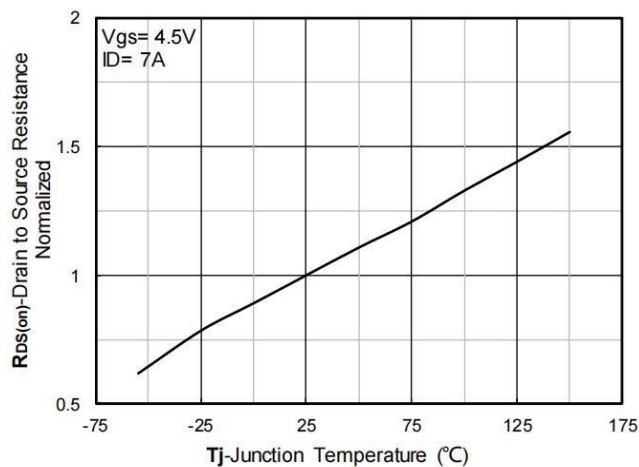


Figure 6. Normalized On-Resistance

Typical Characteristics

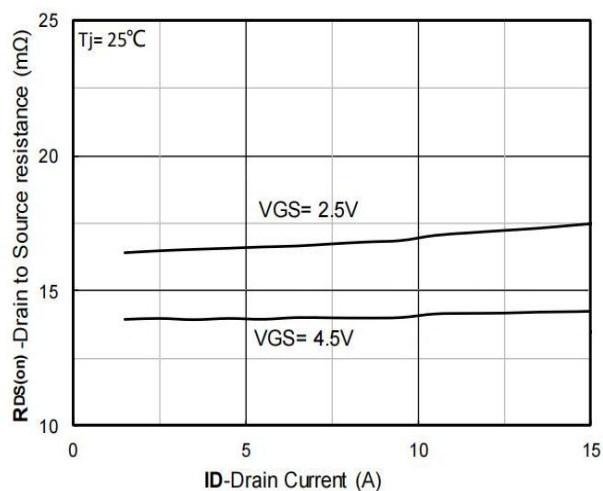


Figure 7. $R_{DS(on)}$ VS Drain Current

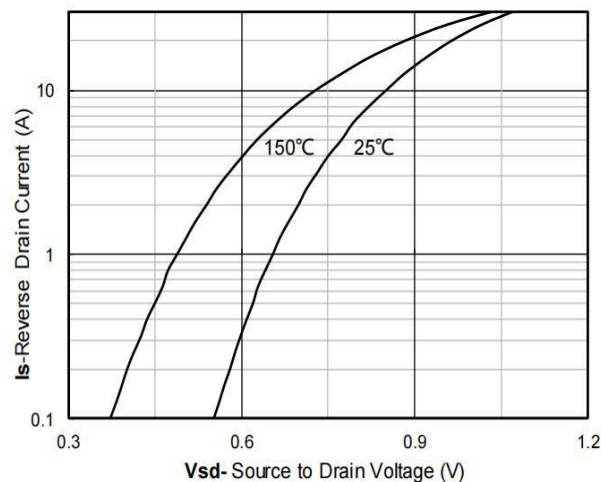


Figure 8. Forward characteristics of reverse diode

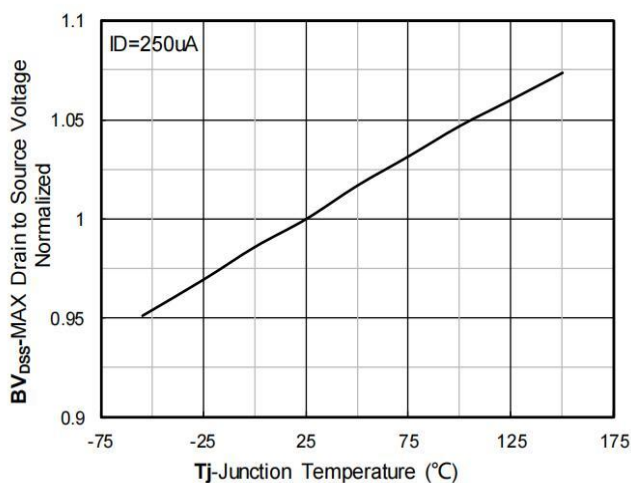


Figure 9. Normalized breakdown voltage

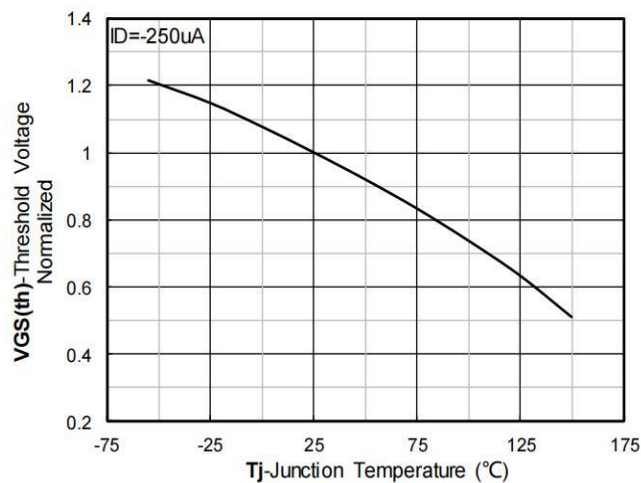


Figure 10. Normalized Threshold voltage

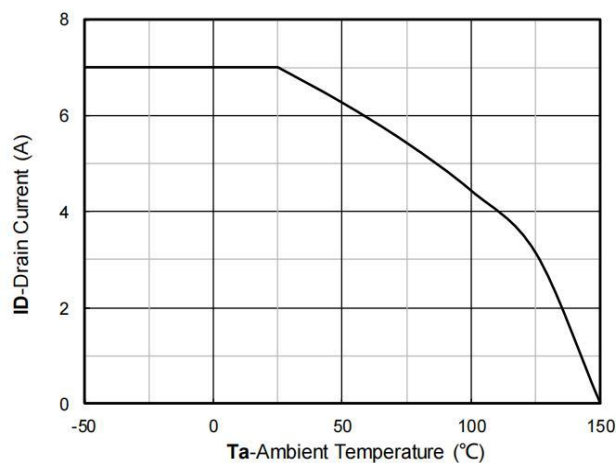


Figure 11. Current dissipation

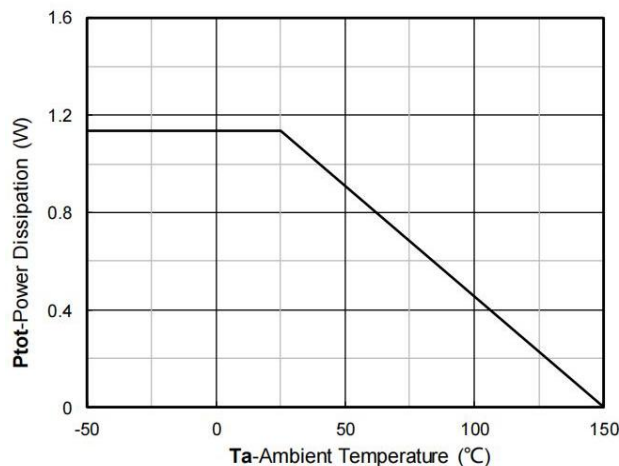


Figure 12. Power dissipation

Typical Characteristics

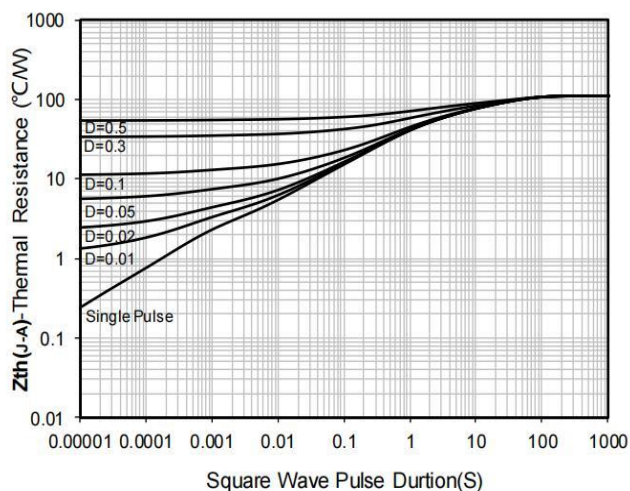


Figure 13. Maximum Transient Thermal Impedance

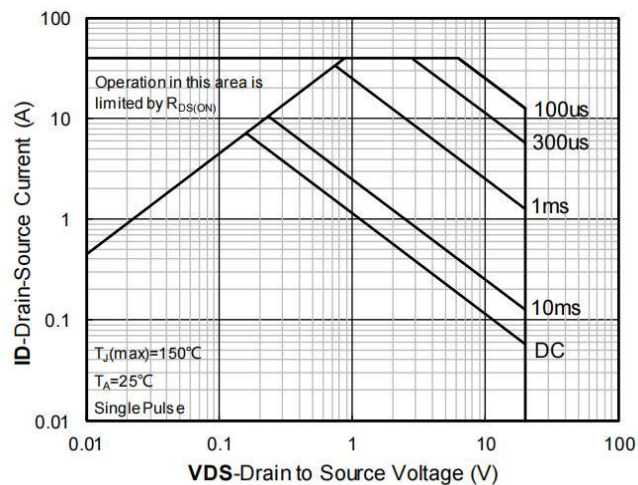
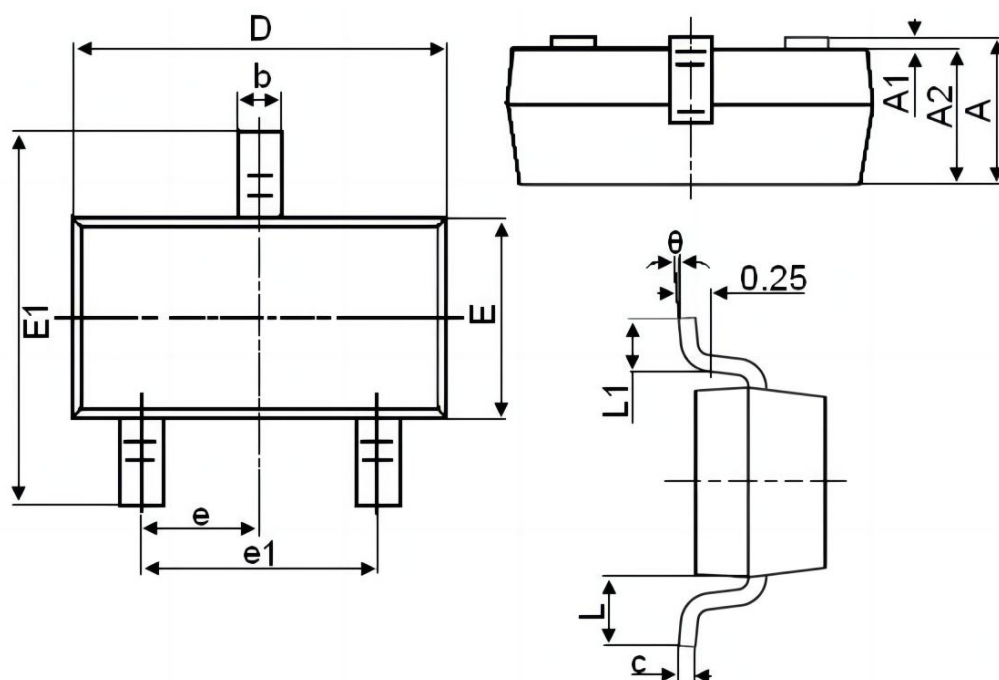


Figure 14. Safe Operation Area

SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°